**Product data sheet** 

# 1. General description

Dual N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1010B-6 (SOT1216) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic-level compatible
- Leadless ultra small and ultra thin SMD plastic package 1.1 x 1.0 x 0.37 mm
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2 kV HBM

# 3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	60	V		
$V_{GS}$	gate-source voltage			-20	-	20	V		
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>sp</sub> = 25 °C		-	-	330	mA		
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	-	260	mA		
Static characteristics (per transistor)									
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = 10 V; $I_D$ = 200 mA; $T_j$ = 25 °C		-	2.2	2.8	Ω		

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.



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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source TR1	500	D1 D2
2	G1	gate TR1	$\begin{bmatrix} 1 \\ 7 \end{bmatrix} \begin{bmatrix} 6 \\ \end{bmatrix}$	
3	D2	drain TR2	2 5	G1 $G2$ $G2$
4	S2	source TR2		
5	G2	gate TR2	3 4	
6	D1	drain TR1	Transparent top view	S1 S2 017aaa256
7	D1	drain TR1	DFN1010B-6 (SOT1216)	
8	D2	drain TR2		

# 6. Ordering information

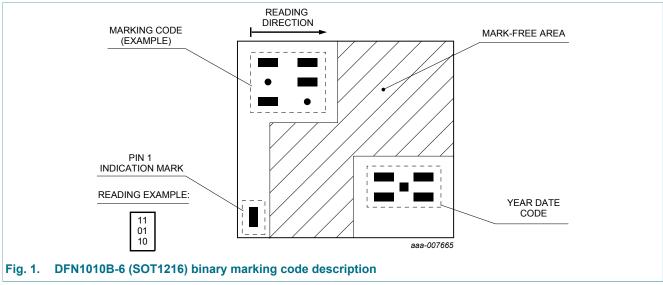
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
NX7002BKXB	DFN1010B-6	DFN1010B-6: plastic thermal enhanced ultra thin small outline package; no leads; 6 terminals	SOT1216		

# 7. Marking

Table 4. Marking codes

Type number	Marking code
NX7002BKXB	00 01 01



NX7002BKXB

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# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor			_	'	-
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> = 25 °C		-	60	V
$V_{GS}$	gate-source voltage			-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{sp}$ = 25 °C		-	330	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 25 °C	[1]	-	260	mA
		V <sub>GS</sub> = 10 V; T <sub>amb</sub> = 100 °C	[1]	-	170	mA
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10 \mu s$		-	0.8	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	285	mW
			[1]	-	407	mW
		$T_{sp} = 25  ^{\circ}C$		-	4032	mW
Source-dra	nin diode					
I <sub>S</sub>	source current	T <sub>amb</sub> = 25 °C	[1]	-	0.2	Α
Per device						
T <sub>j</sub>	junction temperature			-55	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>.

<sup>[2]</sup> Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

### 60 V, dual N-channel Trench MOSFET

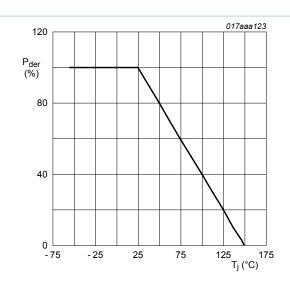


Fig. 2. MOSFET transistor: Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

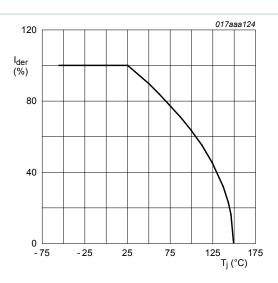
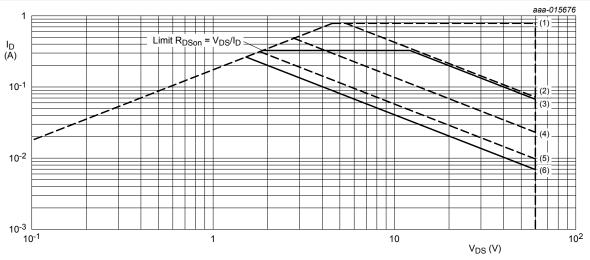


Fig. 3. MOSFET transistor: Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$



I<sub>DM</sub> = single pulse

(1)  $t_p = 10 \mu s$ 

(2)  $t_p = 1 \text{ ms}$ 

(3) DC;  $T_{sp}$  = 25 °C

 $(4) t_p = 10 ms$ 

 $(5) t_p = 100 \text{ ms}$ 

(6) DC; T<sub>amb</sub> = 25 °C; drain mounting pad 1 cm<sup>2</sup>

Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

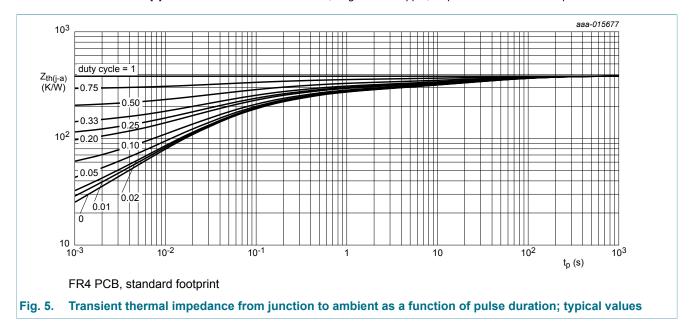
60 V, dual N-channel Trench MOSFET

## **Thermal characteristics**

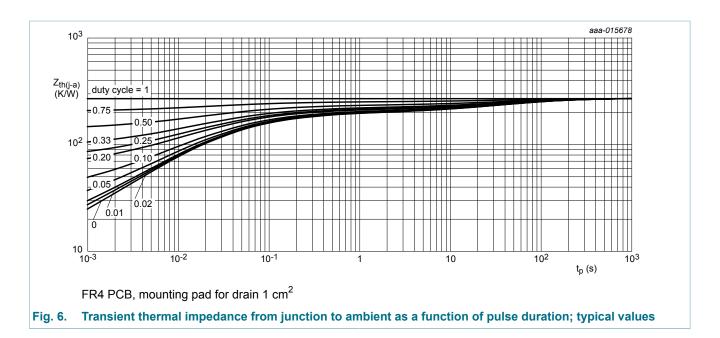
**Thermal characteristics** Table 6.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transist	Per transistor								
R <sub>th(j-a)</sub> thermal resistance from junction to ambient	thermal resistance		[1]	-	276	307	K/W		
			[2]	-	381	438	K/W		
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	27	31	K/W		

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 1 cm<sup>2</sup>. Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.



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## 10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics (per transistor)		,			
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 60 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	10	μΑ
		V <sub>GS</sub> = -20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-10	μA
		V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	1	μΑ
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-1	μΑ
		V <sub>GS</sub> = 5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	0.3	μΑ
		V <sub>GS</sub> = -5 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-0.3	μΑ
R <sub>DSon</sub> drain-source on-staresistance	drain-source on-state	$V_{GS}$ = 10 V; $I_D$ = 200 mA; $T_j$ = 25 °C	-	2.2	2.8	Ω
	resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 150 °C	-	4.5	5.7	Ω
		V <sub>GS</sub> = 5 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	2.5	3.2	Ω
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 200 mA; T <sub>j</sub> = 25 °C	-	600	-	mS
R <sub>G</sub>	gate resistance	f = 1 MHz	-	2.5	-	Ω
Dynamic c	haracteristics (per transist	or)			'	
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 30 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V;	-	1	-	nC
$Q_{GS}$	gate-source charge	T <sub>j</sub> = 25 °C	-	0.12	-	nC
$Q_{GD}$	gate-drain charge		-	0.18	-	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 10 V; f = 1 MHz; V <sub>GS</sub> = 0 V;	-	23.6	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	4.6	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	3	-	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 50 V; I <sub>D</sub> = 200 mA; V <sub>GS</sub> = 10 V;	-	4.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4.3	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	6.9	-	ns
t <sub>f</sub>	fall time	1	-	2.9	-	ns
Source-dra	ain diode (per transistor)		<u> </u>	1	1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 200 mA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.87	1.2	V

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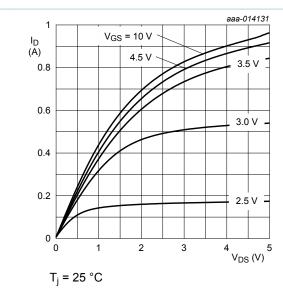


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

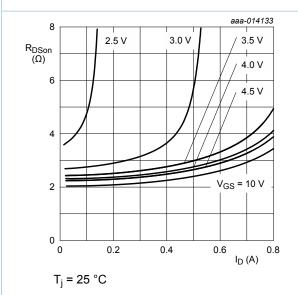
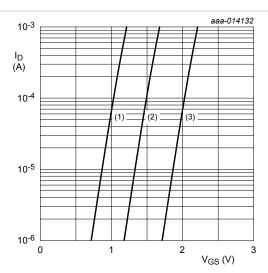


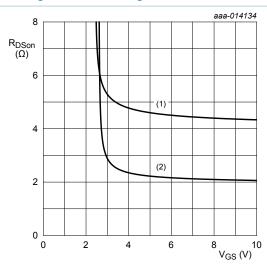
Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



 $T_i = 25 \, ^{\circ}C; \, V_{DS} = 5 \, V$ 

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage



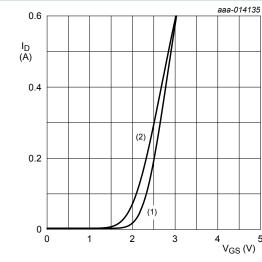
 $I_D = 0.2 A$ 

(1)  $T_i = 150 \, ^{\circ}C$ 

(2)  $T_i = 25 \, ^{\circ}C$ 

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $\mathsf{V}_{\mathsf{DS}} > \mathsf{I}_{\mathsf{D}} \times \mathsf{R}_{\mathsf{DSon}}$ 

(1)  $T_j = 25 \,^{\circ}\text{C}$ (2)  $T_i = 150 \,^{\circ}\text{C}$ 

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

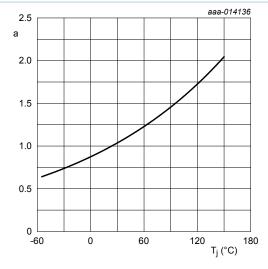
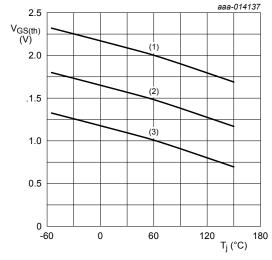


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

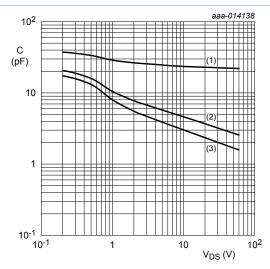
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3)  $C_{rss}$

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 60 V, dual N-channel Trench MOSFET

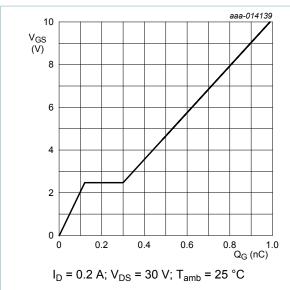


Fig. 15. Gate-source voltage as a function of gate charge; typical values

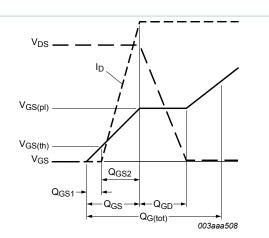
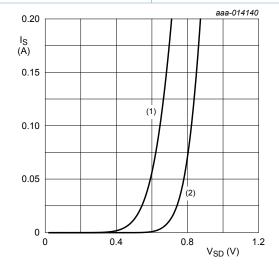


Fig. 16. MOSFET transistor: Gate charge waveform definitions



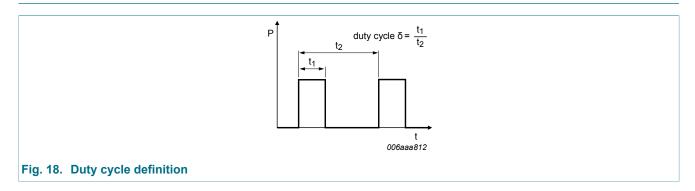
 $V_{GS} = 0 V$ (1)  $T_i = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \,^{\circ}\text{C}$ 

Fig. 17. Source current as a function of source-drain voltage; typical values

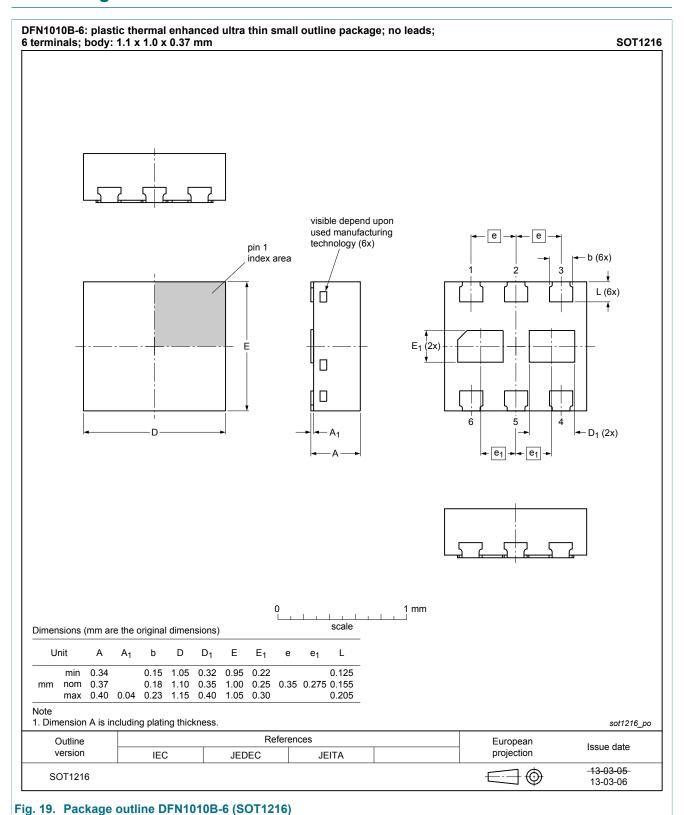
**60 V, dual N-channel Trench MOSFET** 

# 11. Test information



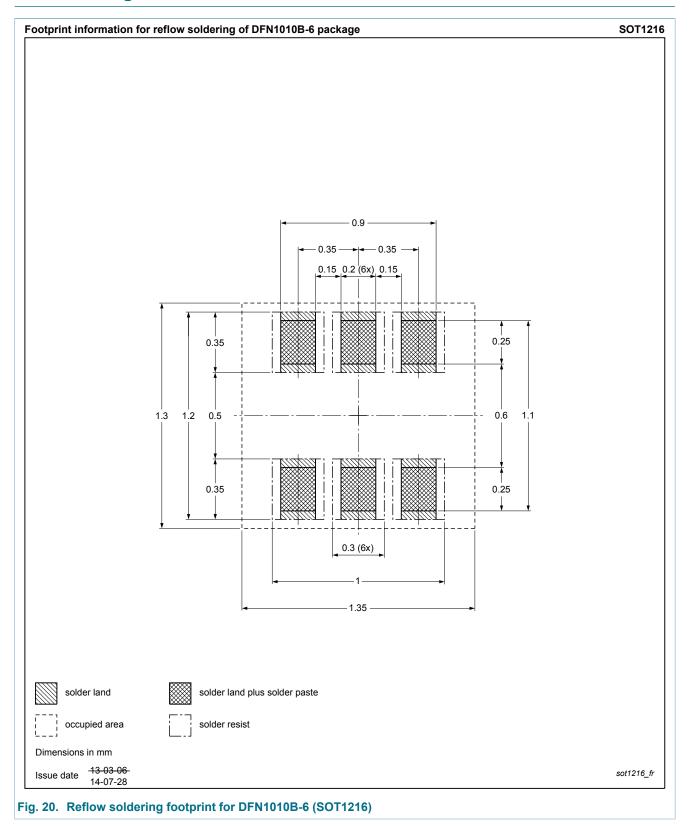
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## 12. Package outline



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# 13. Soldering



NX7002BKXB

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**60 V, dual N-channel Trench MOSFET** 

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
NX7002BKXB v.2	20150630	Product data sheet	-	NX7002BKXB v.1			
Modification:	Modification:  • Change of binary marking code position						
NX7002BKXB v.1	20141210	Product data sheet	-	-			

### 60 V, dual N-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### 60 V, dual N-channel Trench MOSFET

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